DATA SHEET

74LVC2244A

Octal buffer/line driver; with 30 Ω serie termination resistors; 5 V tolerant input/outputs; 3-state

Product specification
Supersedes data of 1999 Sep 30

2002 Jun 18

Philips Semiconductors

PHILIPS

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FEATURES

- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 to 3.6 V
- CMOS low power consumption
- Direct interface with TTL levels
- Inputs accept voltages up to 5.5 V
- Complies with JEDEC standard no. 8-1A
- Integrated 30 Ω termination resistors
- Specified from –40 to +85 °C and –40 to +125 °C.

DESCRIPTION

The 74LVC2244A is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 or 5 V devices. In 3-state operation outputs can handle 5 V. These features allow the use of these devices as translators in a mixed 3.3 and 5 V environment.

The 74LVC2244A is an octal non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs $1\overline{OE}$ and $2\overline{OE}$. A HIGH on $n\overline{OE}$ causes the outputs to assume a high-impedance OFF-state. Schmitt-trigger action at all inputs makes the circuit highly tolerant for slower input rise and fall times. The 74LVC2244A is designed with 30 Ω series termination resistors in both HIGH and LOW output stages to reduce line noise.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; $t_r = t_f \leq 2.5$ ns.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t_{PHL}/t_{PLH}	propagation delay nA_n to nY_n	C_L = 50 pF; V_{CC} = 3.3 V	3.1	ns
C_I	input capacitance		4.0	pF
C_{PD}	power dissipation capacitance per buffer	V_{CC} = 3.3 V; notes 1 and 2	8	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

   $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

   f_i = input frequency in MHz;

   f_o = output frequency in MHz;

   C_L = output load capacitance in pF;

   V_{CC} = supply voltage in Volts;

   $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.
2. The condition is V_I = GND to V_{CC}.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE				
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE
74LVC2244AD	–40 to +125 °C	20	SO	plastic	SOT163-1
74LVC2244ADB	–40 to +125 °C	20	SSOP	plastic	SOT339-1
74LVC2244APW	–40 to +125 °C	20	TSSOP	plastic	SOT360-1

FUNCTION TABLE

See note 1.

INPUT		OUTPUT
$n\overline{OE}$	nA_n	nY_n
L	L	L
L	H	H
H	X	Z

Note

1. H = HIGH voltage level;
   L = LOW voltage level;
   X = don't care;
   Z = high-impedance OFF-state.

PINNING

PIN	SYMBOL	DESCRIPTION
1	$1\overline{OE}$	output enable input (active LOW)
2	$1A_0$	data input
3	$2Y_0$	bus output
4	$1A_1$	data input
5	$2Y_1$	bus output
6	$1A_2$	data input
7	$2Y_2$	bus output
8	$1A_3$	data input
9	$2Y_3$	bus output
10	GND	ground (0 V)
11	$2A_3$	data input
12	$1Y_3$	data output
13	$2A_2$	data input
14	$1Y_2$	data output
15	$2A_1$	data input
16	$1Y_1$	data output
17	$2A_0$	data input
18	$1Y_0$	data output
19	$2\overline{OE}$	output enable input (active LOW)
20	V_{CC}	supply voltage

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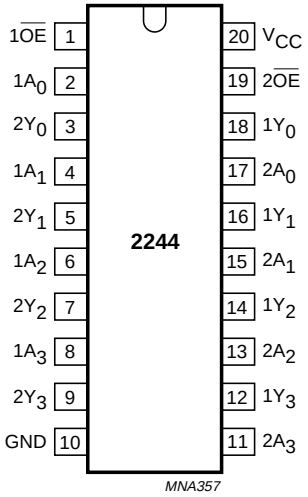


Fig.1 Pin configuration.

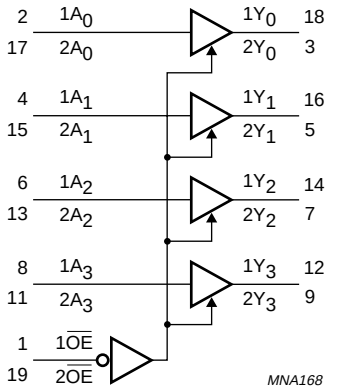


Fig.2 Logic symbol.

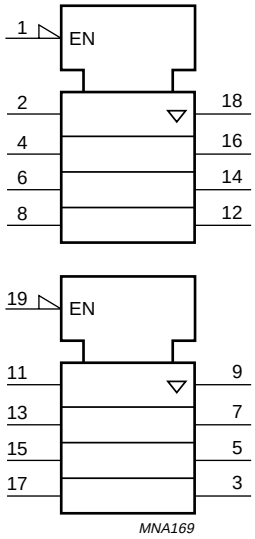


Fig.3 Logic symbol (IEEE/IEC).

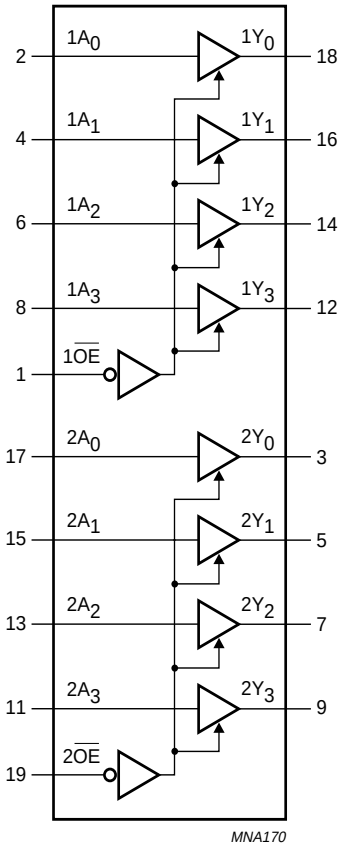


Fig.4 Logic diagram.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage	for maximum speed performance	2.7	3.6	V
		for low-voltage applications	1.2	3.6	V
V_I	input voltage		0	5.5	V
V_O	output voltage	output HIGH or LOW state	0	V_{CC}	V
		output 3-state	0	5.5	V
T_{amb}	operating ambient temperature		–40	+125	°C
t_r, t_f	input rise and fall times	V_{CC} = 1.2 to 2.7 V	0	20	ns/V
		V_{CC} = 2.7 to 3.6 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		–0.5	+6.5	V
I_{IK}	input diode current	$V_I < 0$	–	–50	mA
V_I	input voltage	note 1	–0.5	+6.5	V
I_{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$	–	±50	mA
V_O	output voltage	output HIGH or LOW state; note 1	–0.5	V_{CC} + 0.5	V
		output 3-state; note 1	–0.5	+6.5	V
I_O	output source or sink current	V_O = 0 to V_{CC}	–	±50	mA
I_{CC}, I_{GND}	V_{CC} or GND current		–	±100	mA
T_{stg}	storage temperature		–65	+150	°C
P_{tot}	power dissipation per package				
	SO	above 70 °C derate linearly with 8 mW/K	–	500	mW
	SSOP and TSSOP	above 60 °C derate linearly with 5.5 mW/K	–	500	mW

Note

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

DC CHARACTERISTICS

Over recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		T_{amb} (°C)					UNIT
		OTHER	V_{CC} (V)	–40 to +85			–40 to +125		
				MIN.	TYP.(1)	MAX.	MIN.	MAX.	
V_{IH}	HIGH-level input voltage		1.2	V_{CC}	–	–	V_{CC}	–	V
			2.7 to 3.6	2.0	–	–	2.0	–	V
V_{IL}	LOW-level input voltage		1.2	–	–	0	–	0	V
			2.7 to 3.6	–	–	0.8	–	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; $I_O = -100$ µA	2.7 to 3.6	$V_{CC} - 0.2$	V_{CC}	–	$V_{CC} - 0.3$	–	V
		$V_I = V_{IH}$ or V_{IL}; $I_O = -6$ mA	2.7	$V_{CC} - 0.5$	–	–	$V_{CC} - 0.65$	–	V
		$V_I = V_{IH}$ or V_{IL}; $I_O = -12$ mA	3.0	$V_{CC} - 0.8$	–	–	$V_{CC} - 1$	–	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; $I_O = 100$ µA	2.7 to 3.6	–	0	0.2	–	0.3	V
		$V_I = V_{IH}$ or V_{IL}; $I_O = 6$ mA	2.7	–	–	0.4	–	0.6	V
		$V_I = V_{IH}$ or V_{IL}; $I_O = 12$ mA	3.0	–	–	0.55	–	0.8	V
I_{LI}	input leakage current	$V_I = 5.5$ V or GND	3.6	–	±0.1	±5	–	±20	µA
I_{OZ}	3-state output OFF-state current	$V_I = V_{IH}$ or V_{IL}; $V_O = 5.5$ V or GND	3.6	–	0.1	±10	–	±20	µA
I_{off}	power off leakage supply	V_I or $V_O = 5.5$ V	0.0	–	0.1	±10	–	±20	µA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	3.6	–	0.1	20	–	40	µA
ΔI_{CC}	additional quiescent supply current per in. pin	$V_I = V_{CC} - 0.6$ V; $I_O = 0$	2.7 to 3.6	–	5	500	–	5000	µA

Note

1. All typical values are measured at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C.

AC CHARACTERISTICS

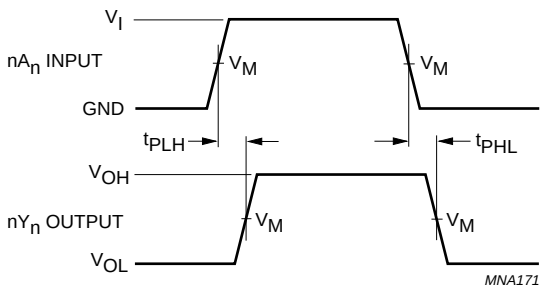
GND = 0 V; $t_r = t_f \leq 2.5$ ns.

SYMBOL	PARAMETER	WAVEFORMS	T_{amb} (°C)					UNIT
			−40 to +85			−40 to +125		
			MIN.	TYP.	MAX.	MIN.	MAX.	
V_{CC} = 1.2 V								
t_{PHL}/t_{PLH}	propagation delay nA_n to nY_n	see Figs 5 and 7	–	35	–	–	–	ns
t_{PZH}/t_{PZL}	3-state output enable time $n\overline{OE}$ to nY_n	see Figs 6 and 7	–	38	–	–	–	ns
t_{PHZ}/t_{PLZ}	3-state output disable time $n\overline{OE}$ to nY_n	see Figs 6 and 7	–	9.0	–	–	–	ns
V_{CC} = 2.7 V								
t_{PHL}/t_{PLH}	propagation delay nA_n to nY_n	see Figs 5 and 7	1.5	3.8	6.4	1.5	8.0	ns
t_{PZH}/t_{PZL}	3-state output enable time $n\overline{OE}$ to nY_n	see Figs 6 and 7	1.5	5.0	8.1	1.5	10.5	ns
t_{PHZ}/t_{PLZ}	3-state output disable time $n\overline{OE}$ to nY_n	see Figs 6 and 7	1.5	5.0	6.4	1.5	8.0	ns
V_{CC} = 3.0 to 3.6 V; note 1								
t_{PHL}/t_{PLH}	propagation delay nA_n to nY_n	see Figs 5 and 7	1.5	3.1	5.5	1.5	7.0	ns
t_{PZH}/t_{PZL}	3-state output enable time $n\overline{OE}$ to nY_n	see Figs 6 and 7	1.0	3.9	7.1	1.0	9.0	ns
t_{PHZ}/t_{PLZ}	3-state output disable time $n\overline{OE}$ to nY_n	see Figs 6 and 7	1.5	2.8	5.4	1.5	7.0	ns
$t_{sk(0)}$	skew	note 2			1.0		1.5	ns

Notes

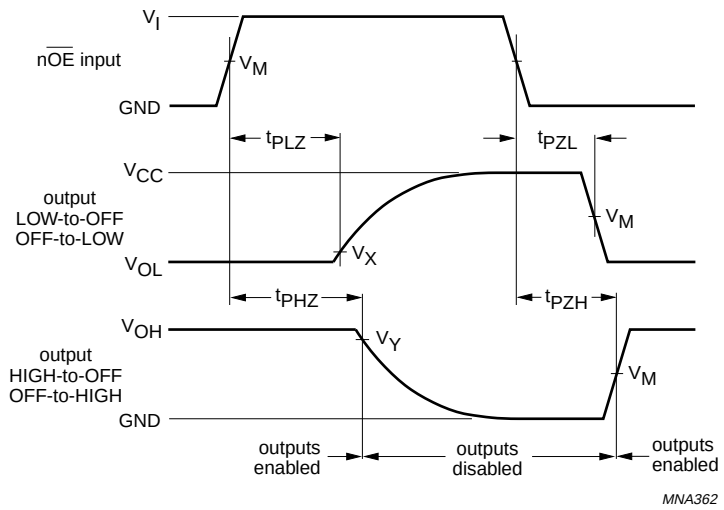
1. Typical values are measured at V_{CC} = 3.3 V.
2. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

AC WAVEFORMS



V_M = 1.5 V at $V_{CC} \geq$ 2.7 V;
$V_M = 0.5V_{CC}$ at V_{CC} < 2.7 V;
V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

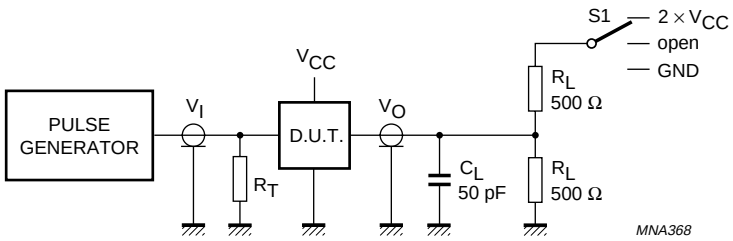
Fig.5 The input nA to output nY propagation delays.



V_M = 1.5 V at $V_{CC} \geq$ 2.7 V;
$V_M = 0.5V_{CC}$ at V_{CC} < 2.7 V;
$V_X = V_{OL}$ + 0.3 V at $V_{CC} \geq$ 2.7 V;
$V_X = V_{OL}$ + 0.1 V at V_{CC} < 2.7 V;
$V_Y = V_{OH}$ − 0.3 V at $V_{CC} \geq$ 2.7 V;
$V_Y = V_{OH}$ − 0.1 V at V_{CC} < 2.7 V.

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.6 3-state enable and disable times.



SWITCH POSITION	
TEST	**S1**
t_{PLH}/t_{PHL}	open
t_{PLZ}/t_{PZL}	2 x V_{CC}
t_{PHZ}/t_{PZH}	GND

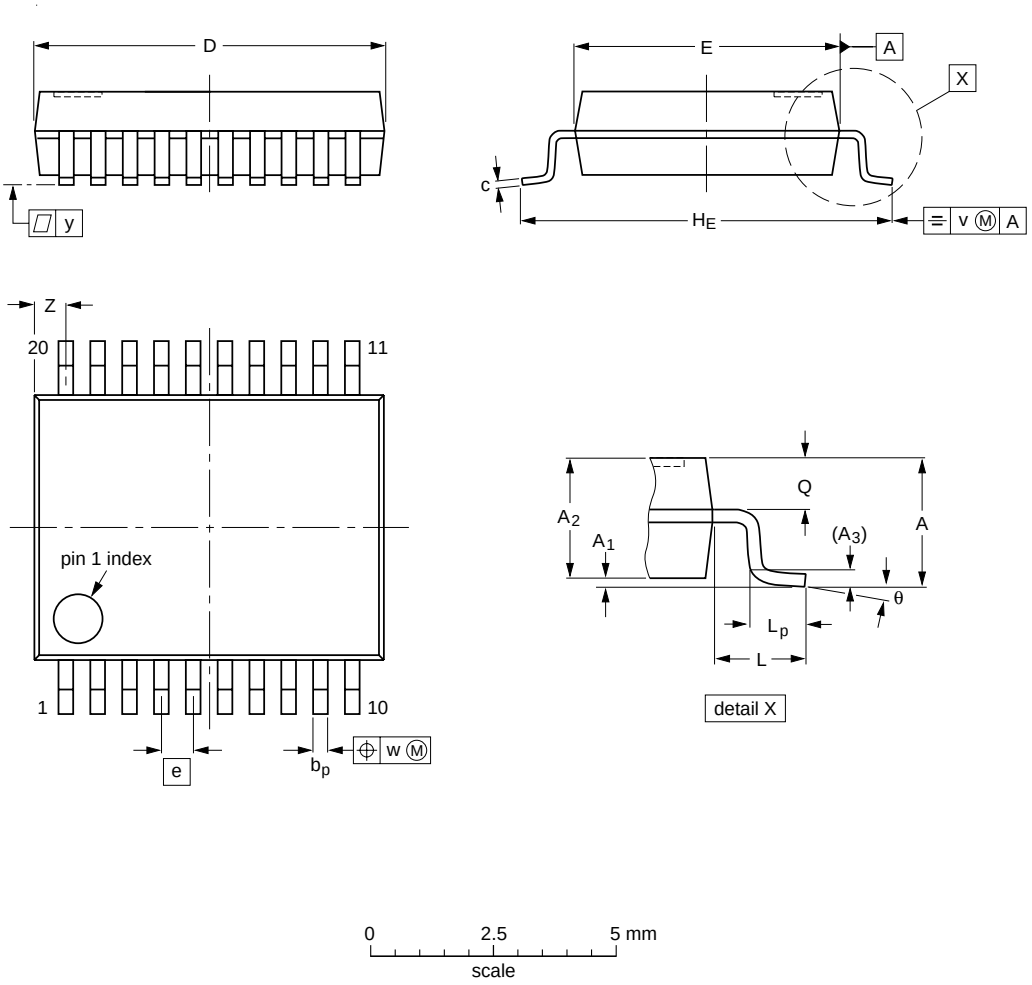
V_{CC}	V_I
< 2.7 V	V_{CC}
2.7 to 3.6 V	2.7 V

Definitions for test circuits:
R_L = Load resistor.
C_L = Load capacitance including jig and probe capacitance.
R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

Fig.7 Load circuitry for switching times.

PACKAGE OUTLINES

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm **SOT339-1**



DIMENSIONS (mm are the original dimensions)

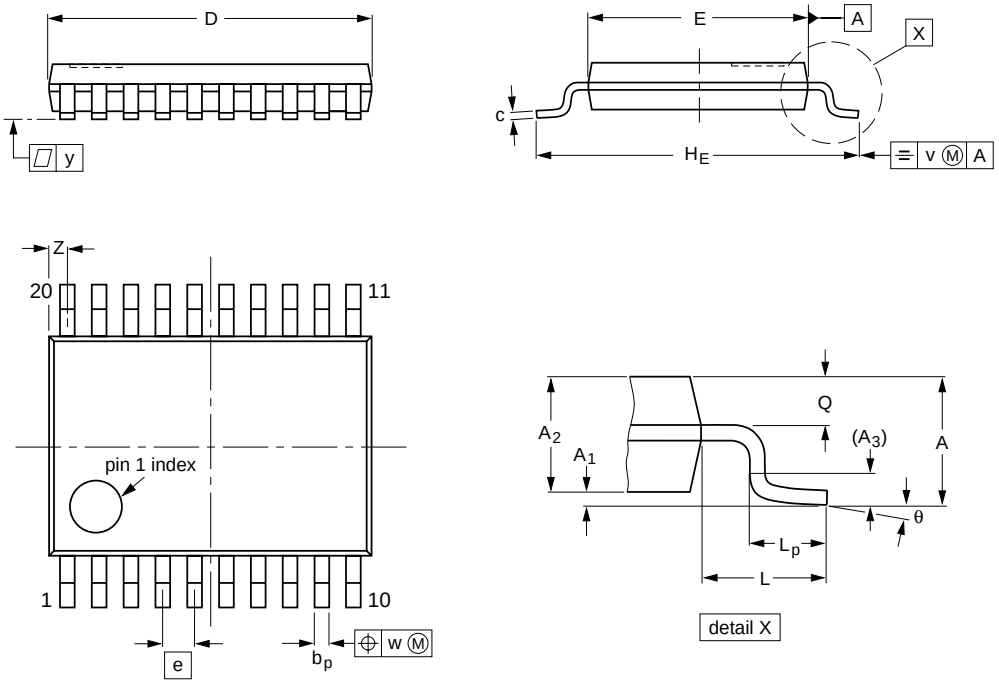
UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8^o 0^o

Note

1. Plastic or metal protrusions of 0.20 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT339-1		MO-150				~~95-02-04~~ 99-12-27

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm **SOT360-1**



DIMENSIONS (mm are the original dimensions)

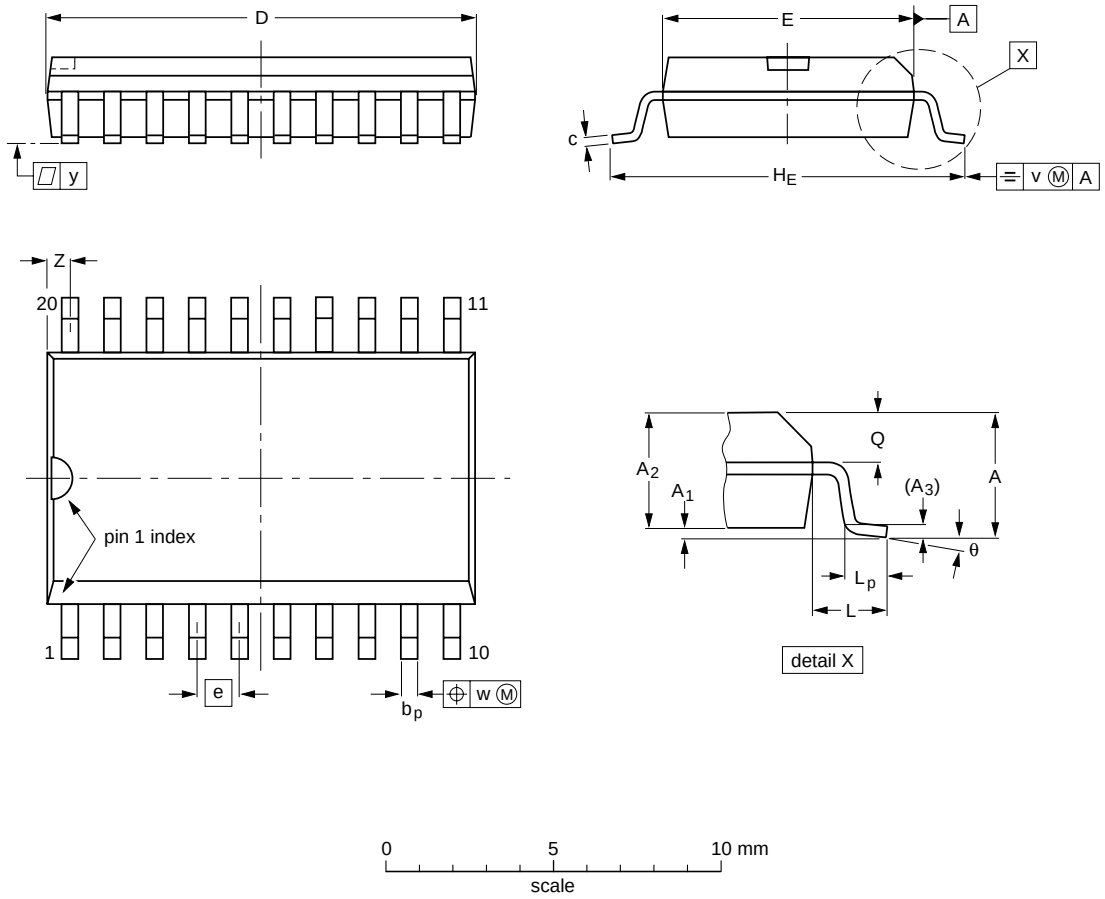
UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT360-1		MO-153				~~95-02-04~~ 99-12-27

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8^o 0^o
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.050	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT163-1	075E04	MS-013				~~97-05-22~~ 99-12-27

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

  The footprint must incorporate solder thieves at the downstream end.
- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.
A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE[1]	SOLDERING METHOD	
	WAVE	REFLOW[2]
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable
HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable[3]	suitable
PLCC[4], SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended[4][5]	suitable
SSOP, TSSOP, VSO	not recommended[6]	suitable

Notes

1. For more detailed information on the BGA packages refer to the *"(LF)BGA Application Note*" (AN01026); order a copy from your Philips Semiconductors sales office.
2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *"Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods"*.
3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
6. Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS(2)	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.
2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

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Printed in The Netherlands 613508/02/pp16 Date of release: 2002 Jun 18 Document order number: 9397 750 09839

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